

# **ISC Silicon NPN Power Transistor**

# **MD2001FX**

## **DESCRIPTION**

- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub>= 700V (Min)
- · High Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

## **APPLICATIONS**

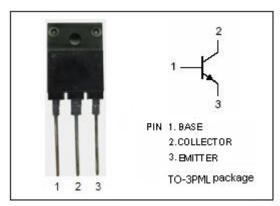
- Horizontal deflection output for monitor and real flat TV
- Switch mode power supplies for CRT TV

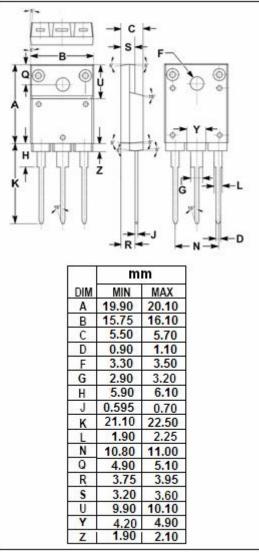
## ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
$V_{CBO}$	Collector-Base Voltage	1500	V
V <sub>CEO</sub>	Collector-Emitter Voltage	700	V
$V_{EBO}$	Emitter-Base Voltage	9	V
Ic	Collector Current- Continuous	12	Α
I <sub>CM</sub>	Collector peak current (tp<5ms)	18	А
I <sub>B</sub>	Base Current- Continuous	6	А
Ртот	Total dissipation at T <sub>c</sub> =25℃	58	W
TJ	Junction Temperature	150	°C
T <sub>stg</sub>	Storage Temperature Range	-65~150	$^{\circ}$

#### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th j-c</sub>	Thermal Resistance, Junction to Case	2.15	°C/W







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#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(sus)</sub> <sup>(1)</sup>	Collector-emitter sustaining Voltage	I <sub>C</sub> = 50mA; I <sub>C</sub> = 0	700			V
V <sub>CE(sat)</sub> <sup>(1)</sup>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 6.0A; I <sub>B</sub> =1.5A			1.8	V
V <sub>BE(sat)</sub> <sup>(1)</sup>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 6.0A; I <sub>B</sub> =1.5A			1.2	<b>V</b>
I <sub>CBO</sub>	Collector Cutoff Current	V <sub>CB</sub> = 1500V ; I <sub>E</sub> = 0 V <sub>CB</sub> = 1500V ; I <sub>E</sub> = 0 ,TC=125			0.2 2	mA
I <sub>EBO</sub>	Emitter Cutoff Current	V <sub>EB</sub> = 9V ; I <sub>C</sub> = 0			1	mA
h <sub>FE-1</sub> <sup>(1)</sup>	DC Current Gain	I <sub>C</sub> = 6A ; V <sub>CE</sub> = 1V		4.5		
h <sub>FE-2</sub> <sup>(1)</sup>	DC Current Gain	I <sub>C</sub> = 6A ; V <sub>CE</sub> = 5V	4.5		7	

#### Switching times

ts	Storage Time  I <sub>CP</sub> = 5A , I <sub>B(on)</sub> = 0.9A ;	2.6	μS	
t <sub>f</sub>	Fall Time	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	0.2	μς

<sup>1.</sup> Pulsed duration =300us,duty cycle ≤1.5%

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